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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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RFMD + TriQuint = Qorvo

QPA0363A

DC to 5000MHz, CASCADABLE SiGe HBT MMIC AMPLIFIER

The QPA0363A is a high performance SiGe HBT MMIC amplifier. A Darlington configuration provides high F_{T} and excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only two DC-blocking capacitors, a bias resistor, and an optional RF choke are required for operation.

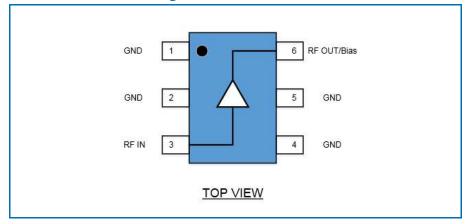


Package: SOT-363

Features

- DC to 5000MHz Operation
- Single Voltage Supply
- Low Current Draw: 11 mA at +5 V Supply
- High Output IP3: +20 dBm typical at 1950 MHz
- Low Noise Figure: 2.85 dB Typical at 1950 MHz

Functional Block Diagram



Applications

- Power Amplifier Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF/RF Buffer Amplifier
- Wireless Data, Satellite

Ordering Information

QPA0363ATR7	7" Reel with 3000 pieces
QPA0363ASQ	Sample Bag with 25 pieces
QPA0363ASR	7" Reel with 100 pieces
QPA0363APCK401	850MHz, +5V Operation PCBA with 5-piece Sample Bag

Preliminary



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Absolute Maximum Ratings

QPA0363A

Parameter	Rating	Units
Device Voltage(V _D)	+4.0	V
Device Current (ID)	22	mA
RF Input Power Note 1	-5	dBm
Storage Temperature	-55 to +150	°C
ESD Rating (HBM)	TBD	-
Moisture Sensitivity Level	MSL1	-

Notes:

- 1. Load Condition 1: $Z_L = 50 \Omega$
- Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in this table.
- 3. Bias Conditions should also satisfy the following expression: $I_DV_D<\!\!(T_J-T_L)/R_{TH},$ and $T_L=\!\!T_{LEAD}.$



Caution! ESD sensitive device.



RFMD Green: RoHS status based on EU Directive 2011/65/EU (at time of this document revision), halogen free per IEC 61249-2-21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional - operation of the device under Absolute Maximum Rating conditions is not implied.

Recommended Operating Conditions

Parameter		Rating			
raiametei	Min	Тур	Max	Units	
Operating Temperature Range	-40		+105	°C	
Junction Temperature (TJ)			+125	°C	
Operating Voltage		+2.5		V	

Electrical Specifications – General

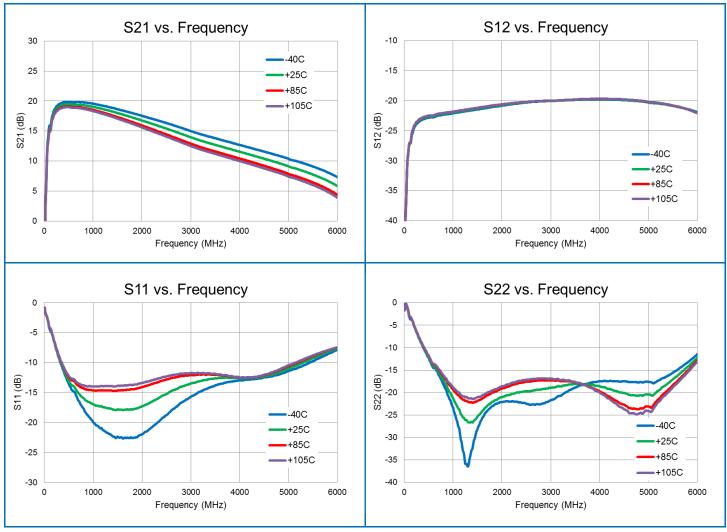
Parameter	Specification		Units	Conditions		
raiailletei	Min	Тур	Max	UIIIIS	Conditions	
		19.3		dB	850MHz	
Small Signal Gain, S21		16.9		dB	1950MHz	
		15.7		dB	2400MHz	
		+1.0		dBm	850MHz	
Output Power at 1 dB Compression		+1.7		dBm	1950MHz	
		+1.7		dBm	2400MHz	
		+16.3		dBm	500MHz	
		+17.5		dBm	850MHz	
Output Third Order Intercept Point		+20.0		dBm	1950MHz	
		+19.0		dBm	2400MHz	
		+16.5		dBm	3500MHz	
Input Return Loss, S11		17.5		dB	1950MHz	
Output Return Loss, S22		21.2		dB	1950MHz	
Reverse Isolation, S12		20.8		dB	1950MHz	
Noigo Figuro		2.60		dB	850MHz	
Noise Figure		2.85		dB	1950MHz	
Device Operating Current		11		mΑ		
Thermal Resistance		TBD		°C/W		

Test Conditions unless otherwise specified: $V_S = +5$ V, $I_D = 11$ mA Typ., OIP3 Tone Spacing=1 MHz, P_{OUT} per tone = -12 dBm, $R_{BIAS} = 220\Omega$ $T_L = +25$ °C, $Z_S = Z_L = 50$ Ω



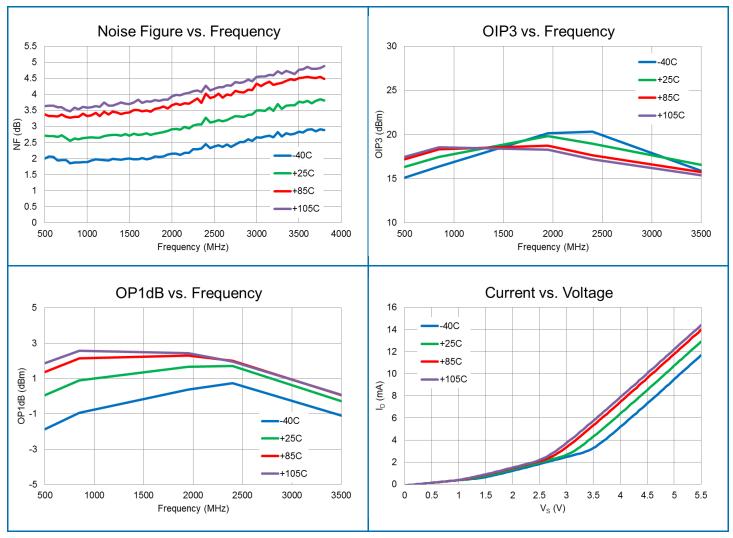
RFMD + TriQuint = Qorvo

Typical Performance Using 850MHz Application Circuit



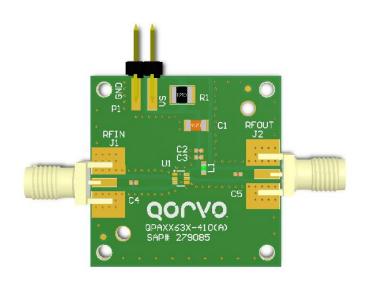


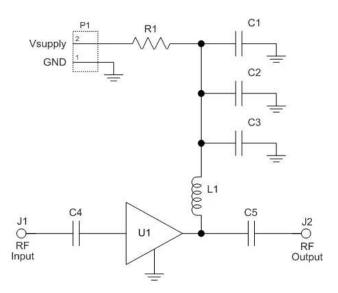
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Evaluation Board and Schematic





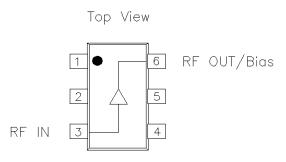
Evaluation Board Bill of Materials For 850MHz Application Circuit

Description	Reference Designator	Manufacturer	Manufacturer's P/N
Gain Block	U1	QORVO	QPA0363A
CAP, 1uF, 10%, 25V, X7R, 1206	C1	Murata Electronics	GRM31MR71E105KA01L
CAP, 1000pF, 10%, 50V, X7R, 0402	C2	Murata Electronics	GRM155R71H102KA01D
CAP, 68pF, 5%, 50V, C0G, 0402	C3	Murata Electronics	GRM1555C1H680JA01D
CAP, 100pF, 5%, 50V, C0G, 0402	C4, C5	Murata Electronics	GRM1555C1H101JA01D
RES, 220 OHM, 5%, 1/2W, 1210	R1	Panasonic Industrial Devices	ERJ-14YJ221U
IND, 33nH, 5%, M/L, 0603	L1	Murata Electronics	LL1608-FSL33NJ
CONN, SMA, EL, FLT, 0.068" SPE-000318	J1. J2	Amphenol RF Asia Corp	901-10426
CONN, HDR, ST, 1x2, 0.100", HI-TEMP, T/H	P1	Samtec Inc.	HTSW-102-07-G-S

Component Values For Specific Frequency and Voltage in Application Circuit

Reference	Frequency (MHz)						
Designator	500	850	1950	2400	3500		
C ₄ , C ₅	220pF 100pF 68pF		56pF	39pF			
C ₃	100pF	68pF	22pF	22pF	15pF		
L ₁	68nH	33nH	22nH	18nH	15nH		
Required Bias Resistance for I _D =11mA Bias Resistance = R _{BIAS} + R _{LDC} = (V _S -V _D) / I _D							
Supply Voltage (Vs)		+5 V	+7.5 V	+9 V	+12 V		
Bias Resistanc	e (R _{1 =} R _{Bias})	220 Ω	470 Ω	620 Ω	910 Ω		
*Note: Bias resistor improves current stability over temperature							

Pin Configuration and Description

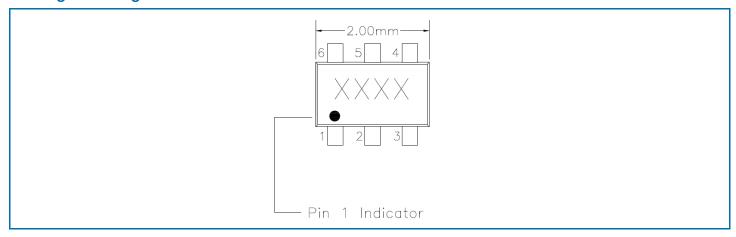


Pin	Label	Description
3	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor as shown in the application schematic.
1, 2, 4, 5	GND	Connect to ground per application circuit drawing. For best performance, vias should be used as shown in the recommended pad layout.
6	RF OUT/BIAS	RF output and bias pin. Bias will be supplied to this pin through an external RF choke. A DC blocking capacitor is necessary on the RF output as shown in the application circuit.

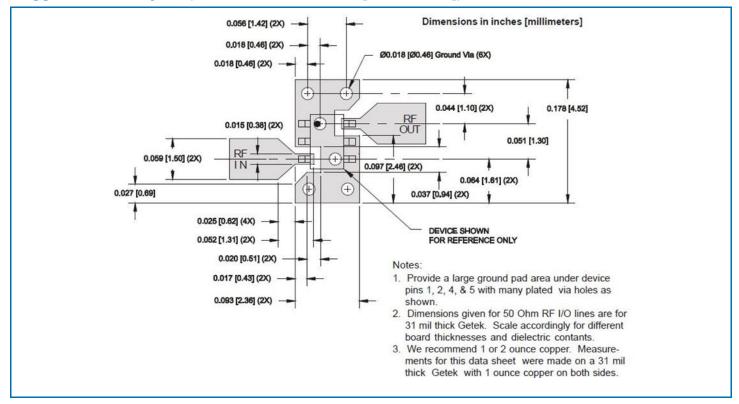


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Package Marking



Suggested Pad Layout (Dimensions in inches [millimeters])

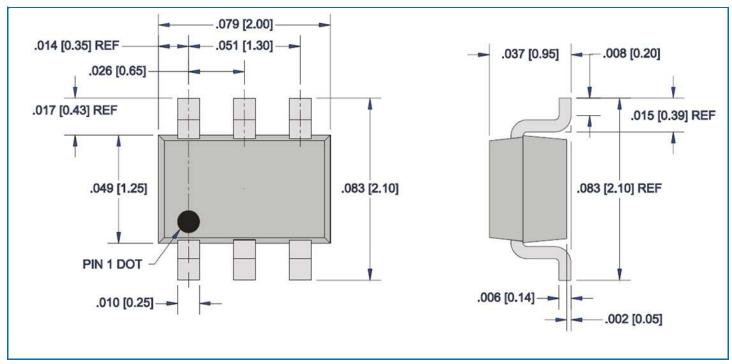






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Package Outline (Dimensions in inches [millimeters])



Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

Web: www.rfmd.com Tel: 1-844-890-8163

Email: customer.support@qorvo.com

For information about the merger of RFMD and TriQuint as Qorvo:

Web: www.qorvo.com

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